

PVT Detector

OVERVIEW

PVT Detector is a unique solution intended to continuously monitor IC status at several on-die locations. It is able to detect manufacturing process deviation, perform voltage and die temperature measurement.

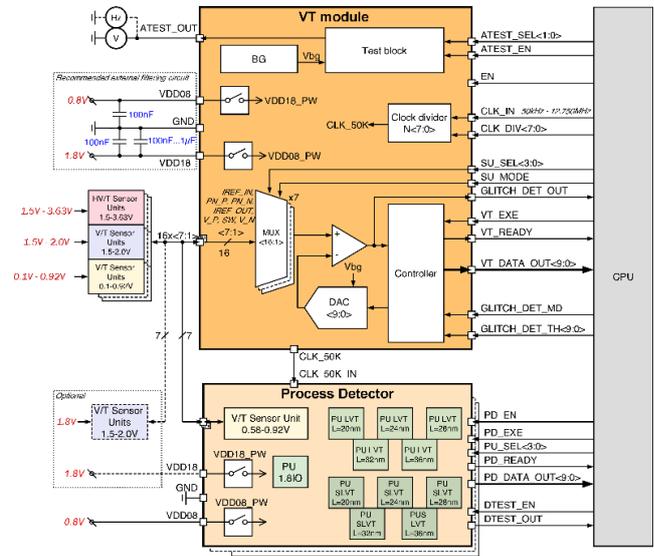
PVT Detector consists of VT module as a calculation center for voltage and temperature measurements, Process detector with process unit for Low VT and Super low VT at different channel length (20, 24, 28, 32, 36 nm) and 1.8V IO transistor, and voltage/temperature sensor units. VT module is able to maintain up to 16 external voltage/ temperature sensor units of three types in any variations: for 0.58V to 0.92V (Core), for 1.5V÷2.0V (IO) and 1.5V÷3.63V (High IO) voltage measurement ranges. Process units can be placed on the die in quantity up to 16 cells. Glitch detector mode allows to monitor and detect rapid fluctuations of voltage and temperature.

IP technology: GF 22nm FDX technology.

IP status: silicon proven.

Area: VT module – 0.12905 mm²; Process detector – 0.0045 mm²;

sensor units for Core/IO/High IO measurements –0.00058 mm²/0.000564 mm²/0.001362 mm²



ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Conditions	Value			Units
			min	typ.	max	
Analog supply voltage	AVDD	-	0.72	0.8	0.88	V
Digital supply voltage	DVDD	-	1.62	1.8	1.98	V
Operating temperature range	T _j	-	-55	27	+150	°C
Current consumption in case of V/T measurement	I _{VDD11_VT}	@VDD08	-	1	20	μA
	I _{VDD33_VT}	@VDD18	-	350	400	
Current consumption in case of process detection	I _{VDD11_P}	@VDD08	-	110	300	μA
	I _{VDD33_P}	@VDD18	-	320	330	
Current consumption in shutdown mode of VT module	I _{STB_VDD11}	@VDD11	-	15	1000	nA
	I _{STB_VDD33}	@VDD33	-	15	400	nA
Output data resolution	K	-	-	10	-	bit
Voltage measurement range	V _{MR08}	-	0.1	-	0.92	V
	V _{MR18}	-	1.5	-	2.0	V
	V _{MR33}	-	1.5	-	3.63	V
Voltage measurement inaccuracy 0.8V/1.8V/3.3V VT sensor unit	A _V	-	-	±2.0/2.0/4.3	-	%
		After trimming	-	±0.8/0.9/3.1	-	
Temperature measurement range	T _{MR}	-	-40	-	+125	°C
Temperature measurement inaccuracy by one/three temperature point on the die	A _T	-	-	±6.4	-	°C
		After trimming	-	±2.3/1.2	-	

*The values correspond to the results of simulations